

RJK0358DPA

Silicon N Channel Power MOS FET Power Switching

REJ03G1651-0400 Rev.4.00 Apr 10, 2008

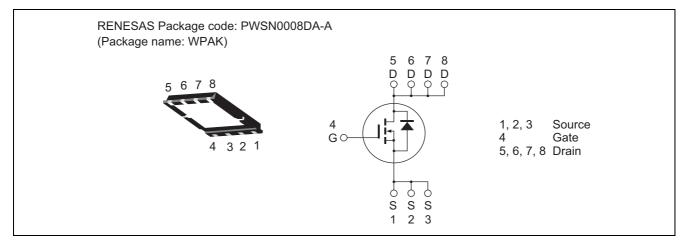
. . . .

Features

- High speed switching
- Capable of 5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance

 $R_{DS(on)} = 2.6 \text{ m}\Omega \text{ typ.}$ (at $V_{GS} = 10 \text{ V}$)

Outline



Absolute Maximum Ratings

		$(Ta = 25^{\circ}C)$
Symbol	Ratings	Unit
V _{DSS}	30	V
V _{GSS}	±20	V
I _D	38	A
Note1 I _{D(pulse)}	152	A
I _{DR}	38	A
I _{AP} Note 2	19	A
E _{AR} Note 2	36.1	mJ
Pch ^{Note3}	45	W
θch-c ^{Note3}	2.78	°C/W
Tch	150	°C
Tstg	-55 to +150	℃
	V _{DSS} V _{GSS} I _D I _{D(pulse)} ^{Note1} I _{DR} I _{AP} E _{AR} Pch θch-c Tch	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tch = 25° C, Rg $\geq 50 \Omega$

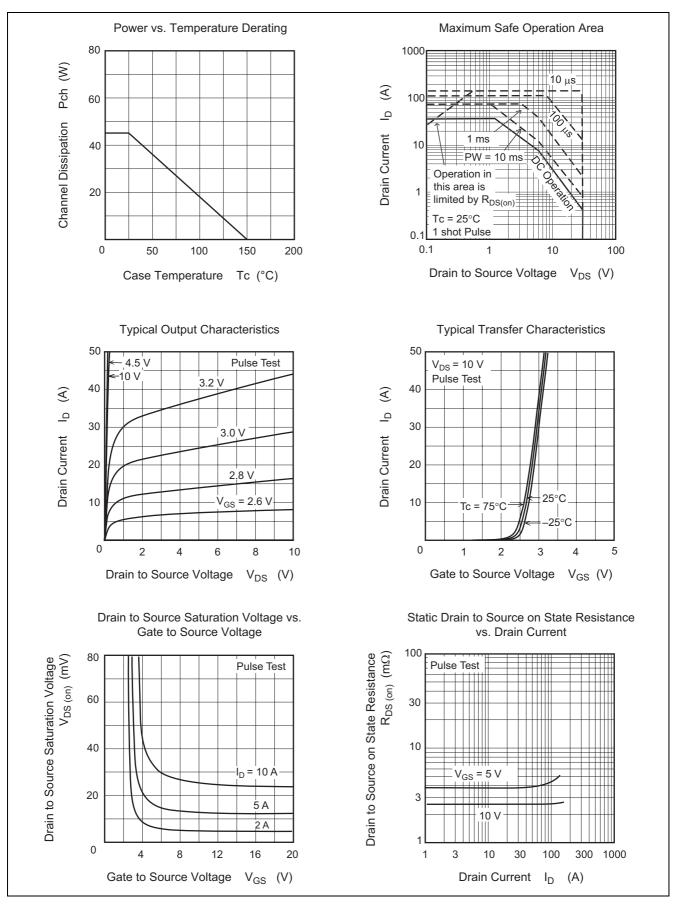
3. Tc = 25°C

Electrical Characteristics

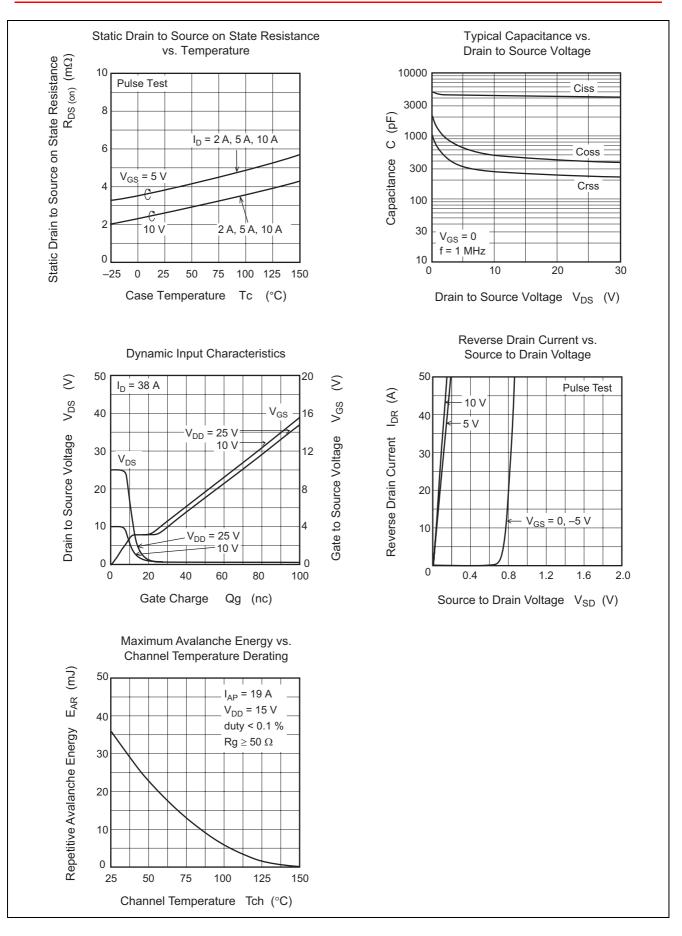
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	30	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	—	± 0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}		—	1	μΑ	$V_{DS} = 30 V, V_{GS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	1.0	—	2.5	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}		2.6	3.4	mΩ	$I_D = 19 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance	R _{DS(on)}		3.8	5.4	mΩ	$I_D = 19 \text{ A}, V_{GS} = 5 \text{ V}^{\text{Note4}}$
Forward transfer admittance	y _{fs}		50	_	S	$I_D = 19 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	4300	_	pF	V _{DS} = 10 V
Output capacitance	Coss		500	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	280	_	pF	
Total gate charge	Qg		33		nC	V _{DD} = 10 V
Gate to source charge	Qgs		13		nC	V _{GS} = 5 V I _D = 38 A
Gate to drain charge	Qgd	_	8	—	nC	
Turn-on delay time	t _{d(on)}	_	11	—	ns	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 19 \text{ A}$
Rise time	tr	_	5.8	—	ns	
Turn-off delay time	t _{d(off)}		68		ns	
Fall time	t _f		12		ns	
Body–drain diode forward voltage	V _{DF}		0.84	1.10	V	$I_F = 38 \text{ A}, V_{GS} = 0^{Note4}$
Body–drain diode reverse recovery	t _{rr}	_	30		ns	$I_F = 38 \text{ A}, V_{GS} = 0$
time						$di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 4. Pulse test

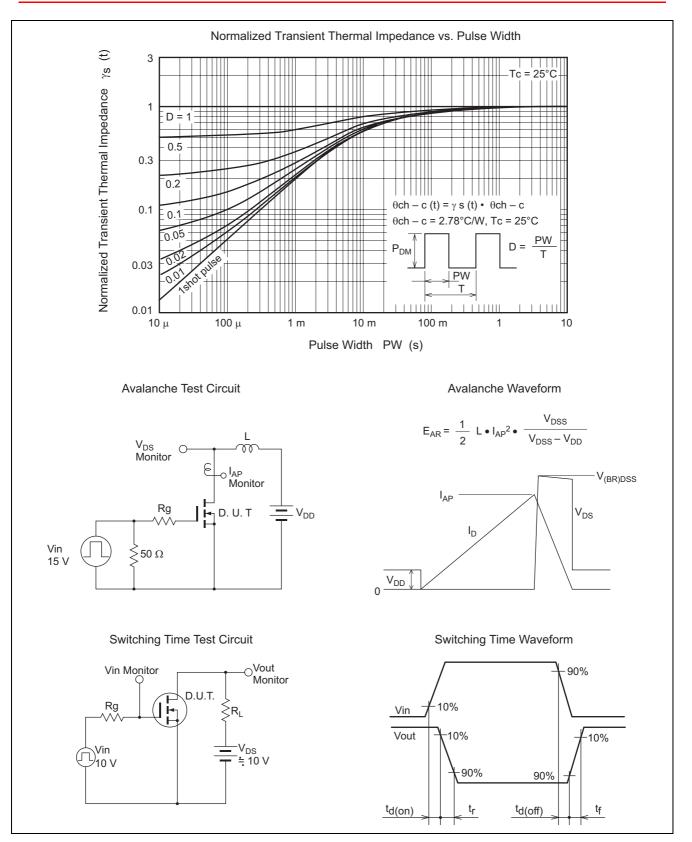
Main Characteristics



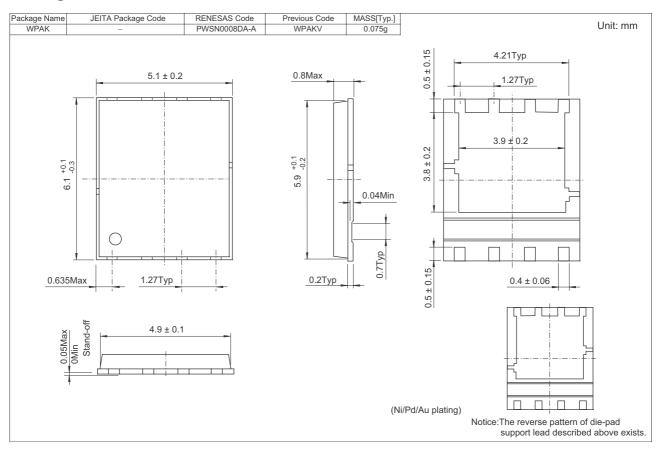
RENESAS



RENESAS



Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK0358DPA-00-J0	2500 pcs	Taping

RenesasTechnology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Benesas lechnology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
 Pines
 This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warranties or representations with respect to the accuracy or completeness of the information in this document.
 But not infinited to, product data. diagrams, charts, programs, algorithms, and application scuch as the development of weapons of mass and regulations, and proceedures required by such laws and regulation.
 All information in this document, included in this document for the purpose of military application scuch as the development of weapons of mass and regulations, and proceedures required by such laws and regulations.
 All information included in this document such as product data, diagrams, charts, programs, algorithms, and application carcuit examples, is current as of the date this document, when exporting the products or the technology described herein, you should follow the applicable export control laws and regulations, and proceedures required by such laws and regulations.
 Renesas has used reasonable care in compiling the information in this document, but Renesas assumes no liability whattowere for any damages incurred as a fast used in this document, but Renesas assumes no liability whattowere of neitary application states are the explorability of the total system before deciding about the applicability or otherwise in systems the failue on malfunction of which may cause a direct threads for the purpose, leave and mediation in the date this document. Jou should evaluate the information in link document to use and regulations.
 When using or otherwise regulations in the information in this document. Dut Renesas as subletion data and applications and regulations and regulations and regulations.
 When using or otherwise regulation the



RENESAS SALES OFFICES

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

http://www.renesas.com